

Silicon NPN Power Transistors

2SC1929

DESCRIPTION

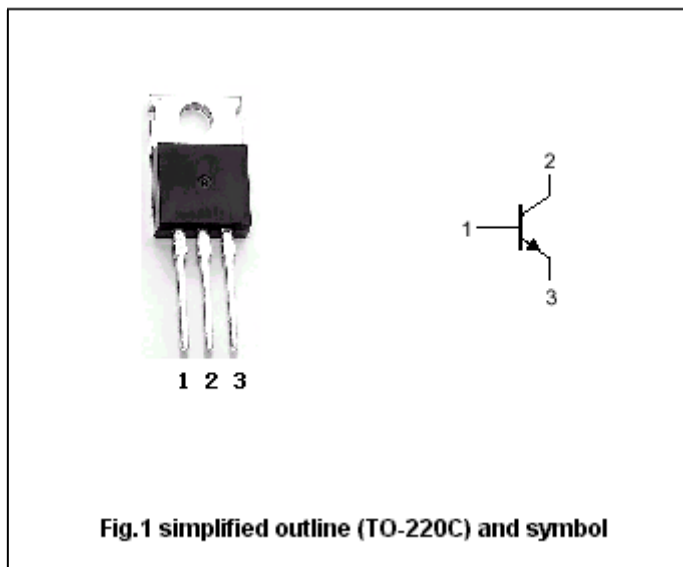
- With TO-220C package
- High V_{CE0}
- Large P_C

APPLICATIONS

- AF output for direct main operation TV

PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

Absolute maximum ratings ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		0.4	A
I_{CM}	Collector current-Peak		1	A
P_C	Total power dissipation	$T_C=25^\circ\text{C}$	25	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =5mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =500mA ; I _B =50mA			2.0	V
V _{BEsat}	Base-emitter on voltage	I _C =0.1A ; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =300V ; I _E =0			10	μ A
h _{FE-1}	DC current gain	I _C =0.1A ; V _{CE} =5V	35		330	
h _{FE-2}	DC current gain	I _C =0.3A ; V _{CE} =5V	30			
f _T	Transition frequency	I _C =0.1A ; V _{CE} =5V		80		MHz

◆ h_{FE-1} Classifications

S	R	Q	P
35-70	60-120	100-200	165-330

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PACKAGE OUTLINE

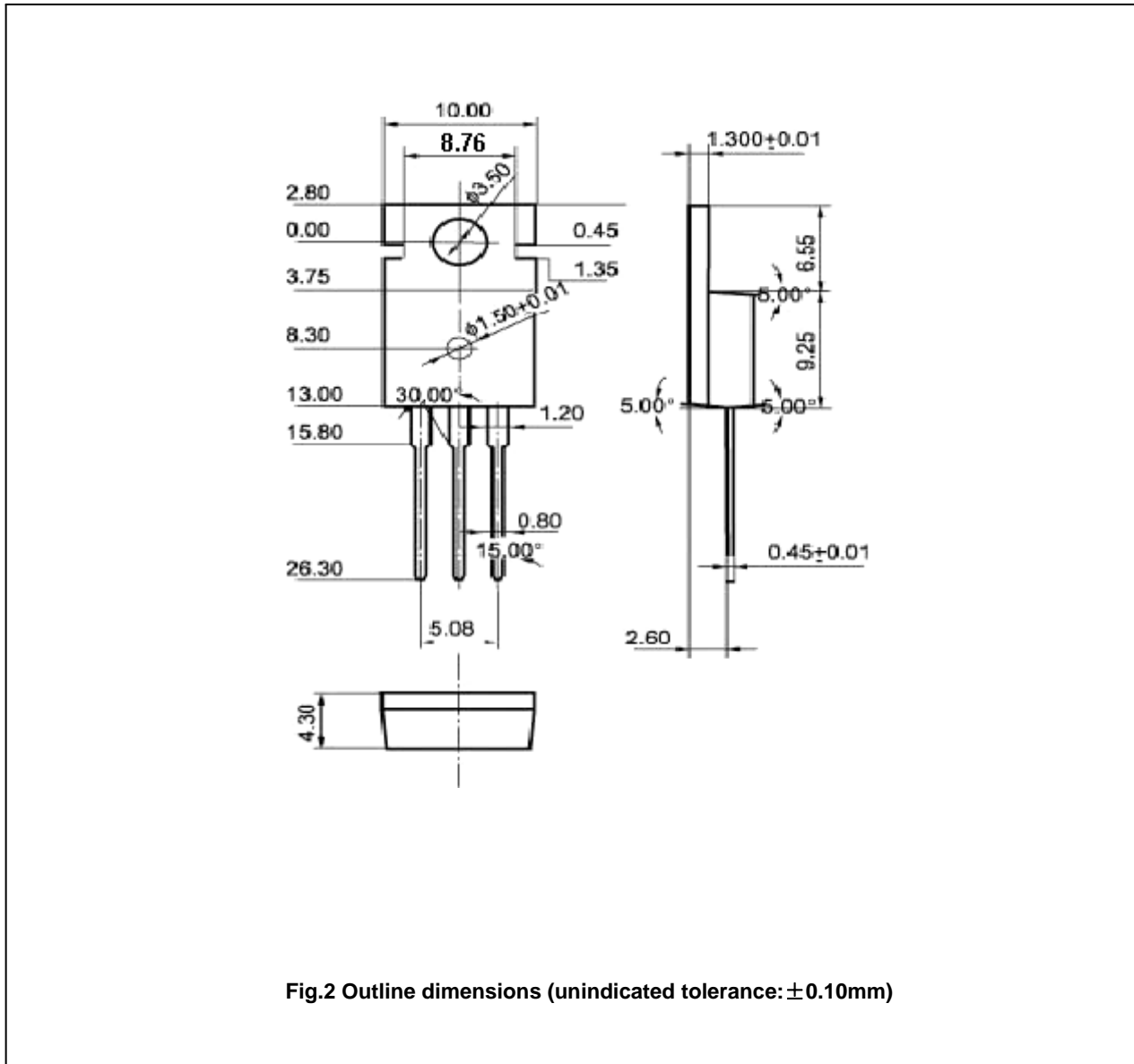


Fig.2 Outline dimensions (unindicated tolerance: ±0.10mm)